

#### INCHANGE SEMICONDUCTOR

# **Isc N-Channel MOSFET Transistor**

### TK42E12N1

RDS( • Enhand Vth = • 100% a • Minimu perform • <b>DESCF</b> • Switchi	ain-source on-resistance: ON) = 9.4mΩ (VGS = 10 V) cement mode: = 2.0 to 4.0V (VDS = 10 V, ID=1.0mA avalanche tested im Lot-to-Lot variations for robust d nance and reliable operation RITION	I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 2 3   I 1 3   I 2 3		
	LUTE MAXIMUM RATINGS(Ta=25		LINUT	
SYMBOL	PARAMETER	VALUE	UNIT	Ĩ <sup>i</sup> ttot
V <sub>DSS</sub>	Drain-Source Voltage	120	v	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
Ι <sub>D</sub>	Drain Current-Continuous	42	А	
I <sub>DM</sub>	Drain Current-Single Pulsed	167	А	
PD	Total Dissipation @Tc=25°C	140	w	DIM MIN MAX
Tj	Max. Operating Junction Temperature	150	°C	A   15.50   15.90     B   9.80   10.20     C   4.20   4.50
T <sub>stg</sub>	Storage Temperature	-55~150	°C	D 0.70 0.90 F 3.40 3.70 G 4.98 5.18
• THERM		H   2.68   2.90     J   0.44   0.60     K   12.80   13.40     L   1.20   1.45		
SYMBOL	PARAMETER	МАХ	UNIT	Q 2.70 2.90 R 2.30 2.70 S 1.29 1.35
Rth(ch-c)	Channel-to-case thermal resistance	0.89	°C/W	U 6.45 6.65 V 8.66 8.86

isc website: www.iscsemi.cn



## Isc N-Channel MOSFET Transistor

### TK42E12N1

#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 10mA	120			V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> = 10V; I <sub>D</sub> =1.0mA	2.0		4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =21A			9.4	mΩ
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 120V; V <sub>GS</sub> = 0V			10	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>DR</sub> =42A, V <sub>GS</sub> = 0 V			1.2	V



#### NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications. ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

2